

L Number	Hits	Search Text	DB	Time stamp
-	0	((("6200867") or ("6313505") or ("6594293"))).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and "silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/08 11:01
-	883	438/197.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:38
-	0	438/197.ccls. and "silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:45
-	106	"silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:37
-	21	"silicon germanium oxide" and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
-	17	"silicon germanium oxide" and epitaxial and deposition	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
-	15	"silicon germanium oxide" and epitaxial and deposition and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
-	14	"silicon germanium oxide" and epitaxial and deposition and gate and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
-	6	((("6200867") or ("6313505") or ("6594293"))).PN. or ((2002/0182815) or (2003/0025163)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:43
-	0	((("6200867") or ("6313505") or ("6594293"))).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and "silicon germanium"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:44
-	1	((("6200867") or ("6313505") or ("6594293"))).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and (silicon with germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:45
-	0	((("6200867") or ("6313505") or ("6594293"))).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and (silicon with germanium) and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:45
-	102	438/197.ccls. and "silicon germanium"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:46
-	99	438/197.ccls. and "silicon germanium" and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:46
-	48	438/197.ccls. and "silicon germanium" and oxide and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:46
-	13	438/197.ccls. and "silicon germanium" and oxide and (epitaxial with deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:46
-	12	438/197.ccls. and "silicon germanium" and oxide and (epitaxial with deposition) and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:00

-	35	"silicon germanium deposition"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:01
-	20	"silicon germanium deposition" and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:01
-	20	"silicon germanium deposition" and epitaxial and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:01
-	8	"silicon germanium deposition" and epitaxial and remov\$4 and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:02
-	6	"silicon germanium deposition" and epitaxial and remov\$4 and gate and etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:02
-	5	"silicon germanium deposition" and epitaxial and remov\$4 and gate and etch\$4 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:02
-	0	"silicon germanium deposition" and epitaxial and remov\$4 and gate and etch\$4 and transistor and protect\$4 and clean	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:03
-	0	"silicon germanium deposition" and epitaxial and remov\$4 and gate and etch\$4 and transistor and protect\$4 and ash\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:03
-	2	"silicon germanium deposition" and epitaxial and remov\$4 and gate and etch\$4 and transistor and protect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:32
-	0	"silicon germanium deposition" and epitaxial and remov\$4 and gate and etch\$4 and transistor and protect\$4 and (wash or clean)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:33
-	0	"silicon germanium oxide" near9 gate and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:38
-	2	"silicon germanium oxide" near9 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:42
-	658	"silicon germanium" near9 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:42
-	231	"silicon germanium" near9 gate and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:42
-	195	"silicon germanium" near9 gate and epitaxial and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:46
-	9131	(oxide near9 gate) and epitaxial and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:46
-	1307	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:46
-	1048	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:47

-	576	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4 and oxidiz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:47
-	150	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4 and oxidiz\$4 and (clean or wash)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:48
-	12	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4 and oxidiz\$4 and (clean or wash) and recess	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:48
-	12	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4 and oxidiz\$4 and (clean or wash) and recess and etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:48
-	12	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4 and oxidiz\$4 and (clean or wash) and recess and etch\$4 and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:49
-	10	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4 and oxidiz\$4 and (clean or wash) and recess and etch\$4 and electrode and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:49
-	10	(oxide near9 gate) and epitaxial and remov\$4 and "silicon germanium" and pattern\$4 and oxidiz\$4 and (clean or wash) and recess and etch\$4 and electrode and dielectric and protect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:49
-	109	"silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 12:51
-	15	"silicon germanium oxide" and gate and epitaxial and above and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/03 12:54
-	2836	dielectric and electrode and protect\$4 and etch\$4 and oxidiz\$4 and expos\$4 and (semiconductor or wafer or substrate) and pattern\$4 and (clean\$4 or wash\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/08 11:51
-	3	dielectric and electrode and protect\$4 and etch\$4 and oxidiz\$4 and expos\$4 and (semiconductor or wafer or substrate) and pattern\$4 and (clean\$4 or wash\$4) and ("silicon germanium oxide" or SiGeO)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/08 11:52